

TSM3442 20V N-Channel MOSFET



SOT-26

654 654

Pin Definition:

- Drain
 Drain
 Drain
 Drain
 Gate
 Source
- PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
20	70 @ V _{GS} = 4.5V	4
	90 @ V _{GS} = 2.5V	3.5

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

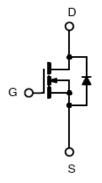
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing		
TSM3442CX6 RF	SOT-26	3Kpcs / 7" Reel		

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current		I _D	4	А
Pulsed Drain Current		I _{DM}	8	Α
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	1.6	Α
Maximum Power Dissipation	Ta = 25°C	Б	1.25	W
	Ta = 75°C	P _D	0.8	
Operating Junction Temperature		TJ	+150	°C
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\Theta_{JF}$	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ _{JA}	80	°C/W

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Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.

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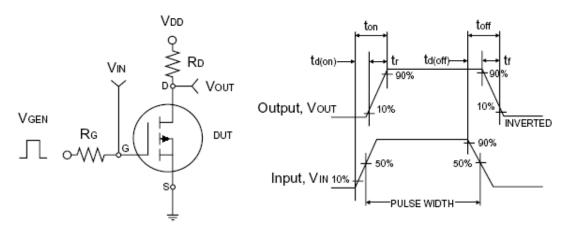


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250 \mu A$	BV _{DSS}	20			V	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	0.65	0.95	1.2	V	
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}	-		±100	nA	
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}	1		1.0	μA	
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	$I_{D(ON)}$	6			Α	
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 4A$	В		50	70	mΩ	
Dialii-Source Oii-State Resistance	$V_{GS} = 2.5V, I_D = 3.5A$	$R_{DS(ON)}$		60	90		
Forward Transconductance	$V_{DS} = 5V, I_D = 2.8A$	g _{fs}		10		S	
Diode Forward Voltage	I _S = 1.6A, V _{GS} = 0V	V_{SD}		0.76	1.2	V	
Dynamic ^b		_					
Total Gate Charge	$V_{DS} = 10V, I_D = 4A,$	Q_g		5.4	10		
Gate-Source Charge	$V_{DS} = 10V, I_D = 4A,$ $V_{GS} = 4.5V$	Q_gs	-	0.65		nC	
Gate-Drain Charge	V _{GS} = 4.5 V	Q_{gd}	-	1.4			
Input Capacitance	\/ - 40\/ \/ - 0\/	C _{iss}	1	340			
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}	1	115		pF	
Reverse Transfer Capacitance	1 - 1.0IVINZ	C_{rss}		33			
Switching ^c							
Turn-On Delay Time	V - 0V D - 400	t _{d(on)}		12	25		
Turn-On Rise Time	$V_{DD} = 6V, R_L = 10\Omega,$	t _r		36	60	nC	
Turn-Off Delay Time	$I_D = 1A$, $V_{GEN} = 4.5V$, $R_G = 6\Omega$	t _{d(off)}		34	60	nS	
Turn-Off Fall Time	1/G = 077	t _f		10	25		

Notes:

- a. pulse test: PW □300μS, duty cycle □2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



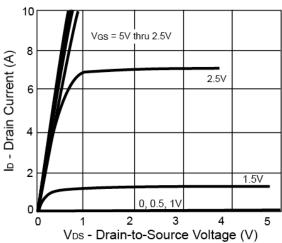
TSM3442

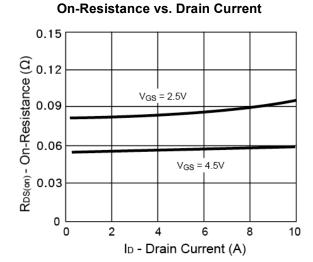
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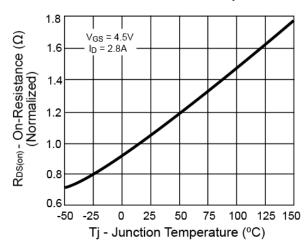
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



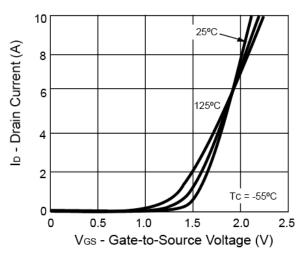




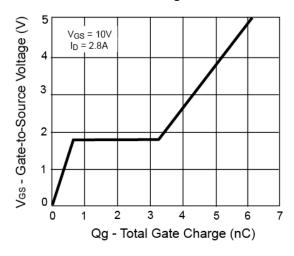
On-Resistance vs. Junction Temperature



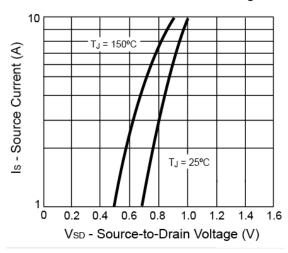
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



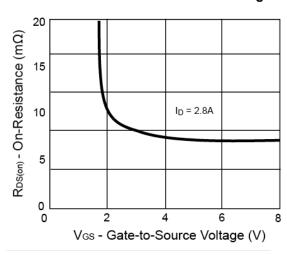


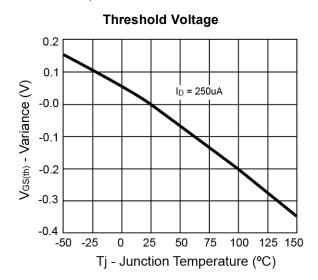




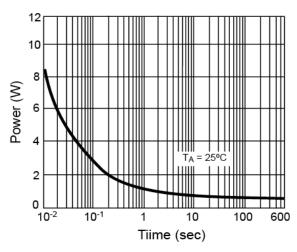
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

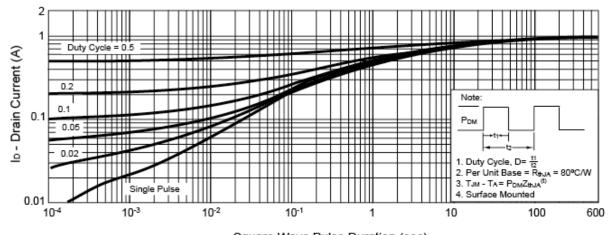




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



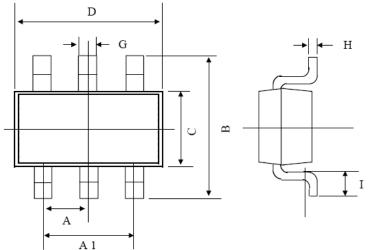
Square Wave Pulse Duration (sec)



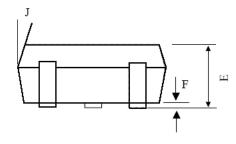


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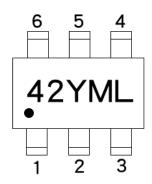
SOT-26 Mechanical Drawing



	SOT-26 DIMENSION						
DIM	MILLIMETERS		INCHES				
DIIVI	MIN	TYP	MAX	MIN	TYP	MAX	
Α	0.95 BSC			0	.0374 BS	С	
A1	1.9 BSC			0.0748 BSC			
В	2.60	2.80	3.00	0.1024	0.1102	0.1181	
С	1.40	1.50	1.70	0.0551	0.0591	0.0669	
D	2.80	2.90	3.10	0.1101	0.1142	0.1220	
Е	1.00	1.10	1.20	0.0394	0.0433	0.0472	
F	0.00		0.10	0.00		0.0039	
G	0.35	0.40	0.50	0.0138	0.0157	0.0197	
Н	0.10	0.15	0.20	0.0039	0.0059	0.0079	
I	0.30		0.60	0.0118		0.0236	
J	5°		10°	5°		10°	



Marking Diagram



42 = Device Code

Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code

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